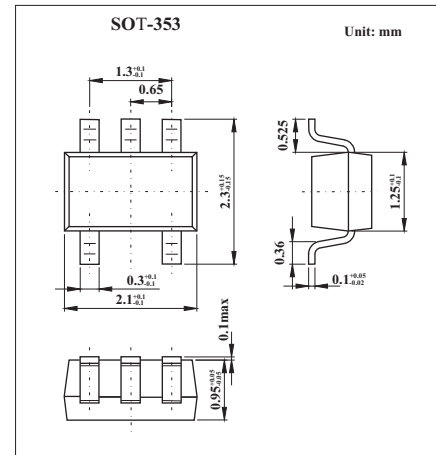
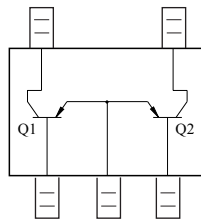


## General purpose (Dual PNP Transistors) KTA501U

### ■ Features

- Power dissipation:  $P_c=200\text{mW}$
- Collector Curren:  $I_c=-150\text{mA}$



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-50	V
Collector-Emitter Voltage	$V_{CE0}$	-50	V
Emitter-Base Voltage	$V_{EB0}$	-5.0	V
Collector Current -Continuous	$I_C$	-150	mA
Collector Power Dissipation(TOTAL)	$P_c$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	$V_{(BR)CB0}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector-to-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-to-base breakdown voltage	$V_{(BR)EB0}$	$I_E = -100\mu\text{A}, I_C = 0$	-5.0			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector cutoff current	$I_{EBO}$	$V_{CE} = -5.0\text{V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -6\text{V}, I_C = -2.0\text{mA}$	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -1\text{mA}, f = 100\text{MHz}$	80			MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			7	pF
Noise Figure	NF	$V_{CE} = -6\text{V}, I_C = -0.1\text{mA}, f = 1\text{KHz}, R_g = 10\text{K}\Omega$		1	10	dB

### ■ hFE Classification

Marking	SY	SGR
Rank	Y	GR
Range	120~240	200~400